All of these share a feature with...



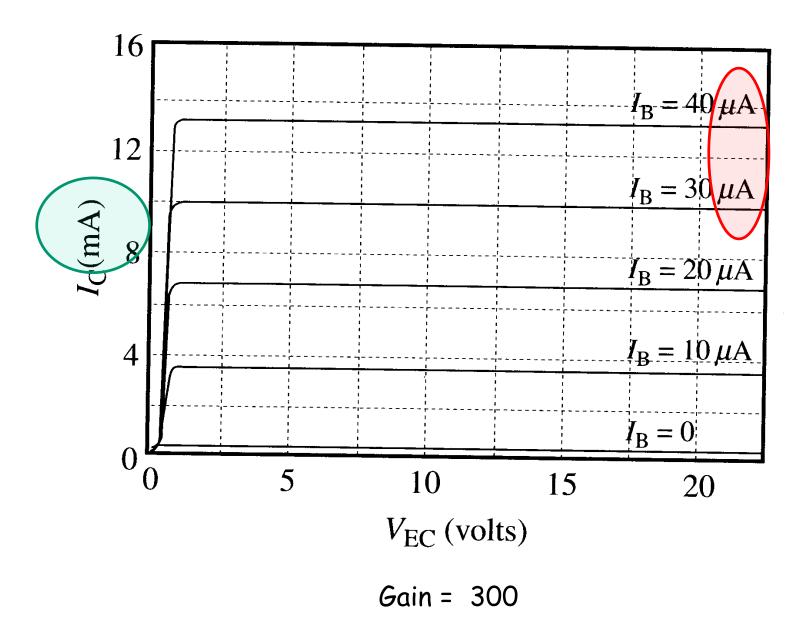
Output current can toggle between large and small

(Switching \rightarrow Digital logic; create 0s and 1s)

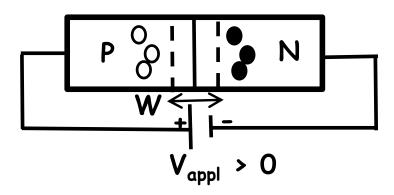
• Small change in 'valve' (3rd terminal) creates Large change in output between 1st and 2nd terminal

(Amplification \rightarrow Analog applications; Turn 0.5 \rightarrow 50)

Example: BJT common emitter characteristics

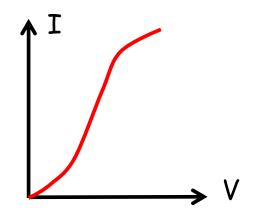


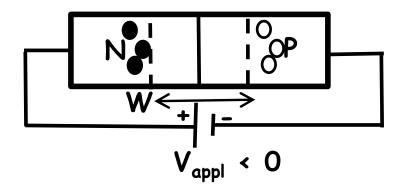
Recall p-n junction



Forward bias, + on P, - on N (Shrink W, V_{bi})

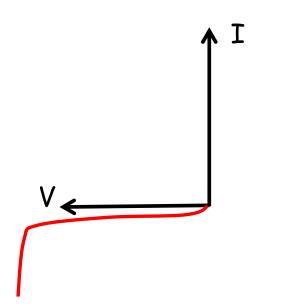
Allow holes to jump over barrier into N region as minority carriers



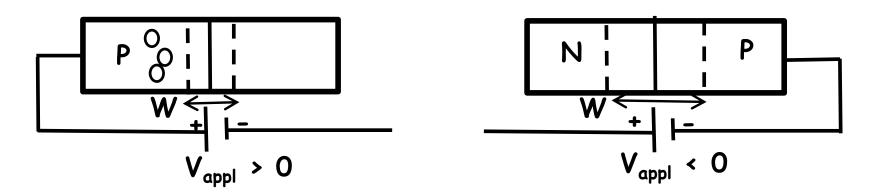


Reverse bias, + on N, - on P (Expand W, V_{bi})

Remove holes and electrons away from depletion region



So if we combine these by fusing their terminals...

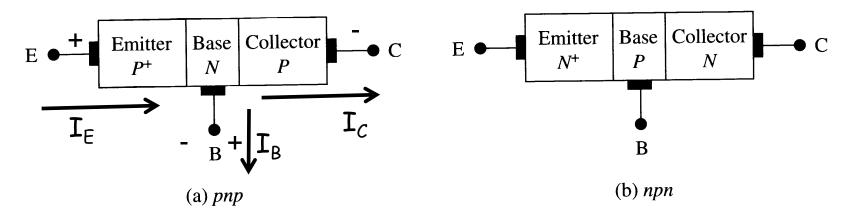


Holes from P region ("Emitter") of 1st PN junction driven by FB of 1st PN junction into central N region ("Base")

Driven by RB of 2nd PN junction from Base into P region of 2nd junction ("Collector")

- · 1st region FB, 2nd RB
- If we want to worry about holes alone, need P+ on 1st region
- · For holes to be removed by collector, base region must be thin

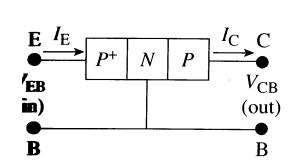
Bipolar Junction Transistors: Basics



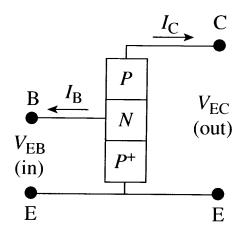
$$I_E = I_B + I_C$$
(KCL)

$$V_{EC} = V_{EB} + V_{BC}$$
 (KVL)

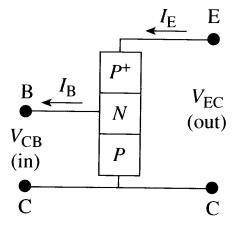
BJT configurations



(a) Common base



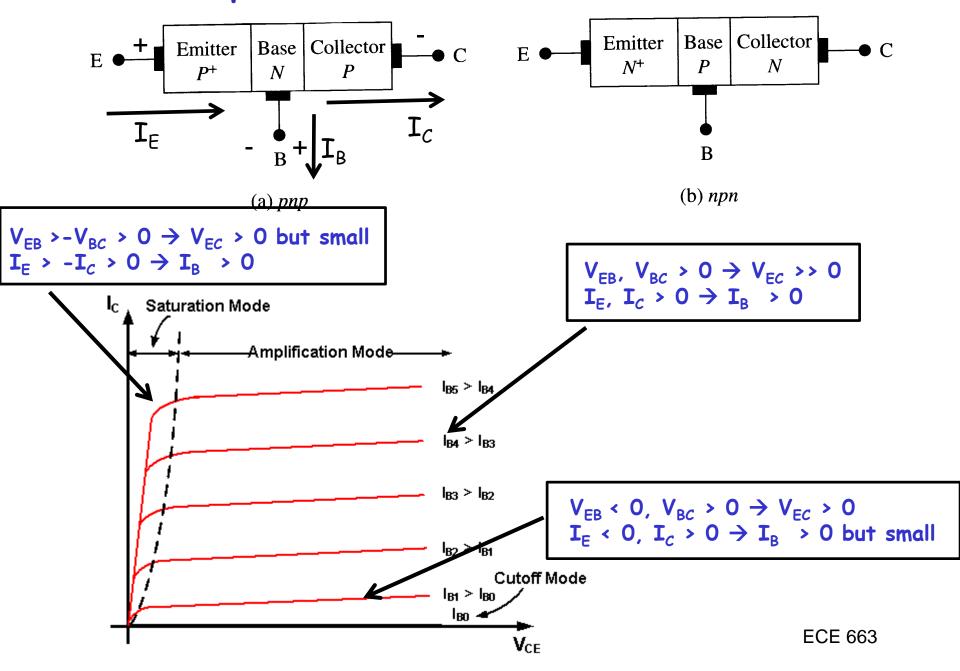
(b) Common emitter



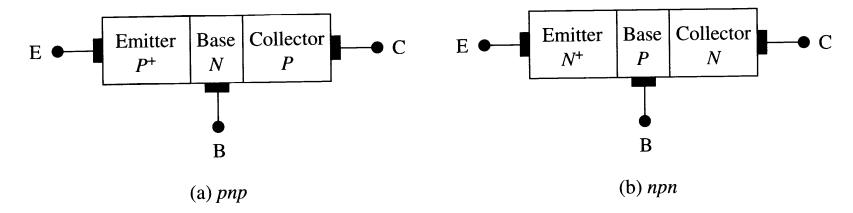
(c) Common collector

GAIN CONFIG

Bipolar Junction Transistors: Basics



Bipolar Junction Transistors: Basics



Bias Mode	E-B Junction	C-B Junction
Saturation	Forward	Forward
Active	Forward	Reverse
Active Inverted	Forward Reverse	Reverse Forward

BJT Fabrication

